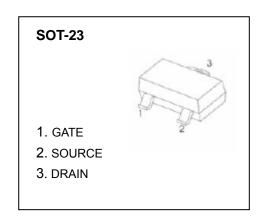


## JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

# **GCH!&' Plastic-Encapsulate MOSFETS**

CJ&''' D-channel MOSFET

V(BR)DSS	RDS(on)MAX	I <sub>D</sub>
	28mΩ@-4.5V	
	32mΩ@-3.7V	
-12V	40mΩ@-2.5V	-6A
	63mΩ@-1.8V	
	150mΩ@-1.5V	



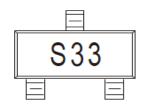
#### **FEATURE**

- TrenchFET Power MOSFET
- Excellent R<sub>DS(on)</sub> and Low Gate Charge

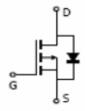
#### **APPLICATION**

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

#### **MARKING**



## **Equivalent Circuit**



#### ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	-12	V
Gate-Source Voltage	V <sub>GS</sub>	±8	V
Continuous Drain Current	I <sub>D</sub>	-6 <sup>a</sup>	Α
Pulsed Drain Current (t=300µs)	I <sub>DM</sub>	-20	Α
Dower Discipation	D	0.35 <sup>b</sup>	W
Power Dissipation	P <sub>D</sub>	1.1 <sup>a</sup>	W
Thermal Resistance from Junction to Ambient	В	357 <sup>b</sup>	°C/W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	113 <sup>a</sup>	°C/W
Junction Temperature	TJ	150	°C
Storage Temperature	T <sub>STG</sub>	-55~ +150	°C

- a. Device mounted on FR-4 substrate board, with minimum recommended pad layout, single side.
- b. Device mounted on no heat sink.

## **MOSFET ELECTRICAL CHARACTERISTICS**

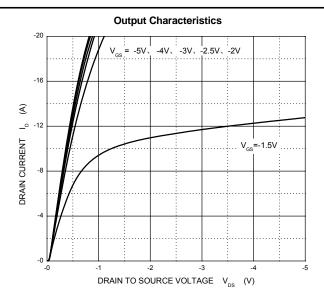
## $T_a$ =25 $^{\circ}$ C unless otherwise specified

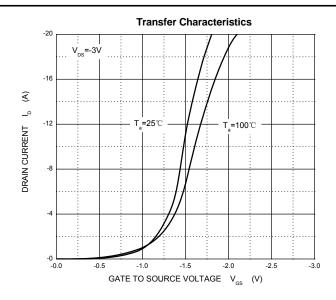
Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V(BR)DSS	V <sub>GS</sub> = 0V, I <sub>D</sub> =-250µA	-12			V
Zero gate voltage drain current	IDSS	V <sub>DS</sub> =-12V,V <sub>GS</sub> = 0V			-1	μΑ
Gate-body leakage current	Igss	V <sub>GS</sub> =±8V, V <sub>DS</sub> = 0V			±0.1	μA
Gate threshold voltage (note 1)	VGS(th)	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-0.4		-1	V
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-5A			28	
		V <sub>G</sub> S =-3.7V, I <sub>D</sub> =-4.6A			32	
Drain-source on-resistance (note 1)	RDS(on)	V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-4.3A			40	mΩ
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-1A			63	
		V <sub>GS</sub> =-1.5V, I <sub>D</sub> =-0.5A			150	
Forward tranconductance (note 1)	<b>g</b> FS	V <sub>DS</sub> =-5V, I <sub>D</sub> =-5A		18		S
Dynamic characteristics (note 2)						
Input Capacitance	C <sub>iss</sub>			1275		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-6V,V <sub>GS</sub> =0V,f =1MHz		255		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			236		pF
Gate resistance	Rg	f=1MHz	1.9	1.9		Ω
Total Gate Charge	Qg			14	21	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-6V,V <sub>GS</sub> =-4.5V,I <sub>D</sub> =-5A		2.3		nC
Gate-Drain Charge	$Q_{gd}$			3.6		nC
Turn-on delay time	<b>t</b> d(on)			26	40	ns
Turn-on rise time	tr	$V_{DD}$ =-6V, $V_{GEN}$ =-4.5V, $I_{D}$ =-4A		24	40	ns
Turn-off delay time	td(off)	$R_L$ =6 $\Omega$ , $R_{GEN}$ =1 $\Omega$		45	70	ns
Turn-off fall time	tf			20	35	ns
Source-Drain Diode characteristics						
Diode forward current	Is	T <sub>C</sub> =25°C			-1.4	Α
Diode pulsed forward current	I <sub>SM</sub>				-20	Α
Diode Forward voltage (note 1)	V <sub>DS</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-4A			-1.2	V
Diode reverse recovery time (note 2)	t <sub>rr</sub>	L - 40 d1/dt-1000/		24	48	ns
Diode reverse recovery charge (note 2)	Qrr	- I <sub>F</sub> =-4A,dI/dt=100A/μs		8	16	nC

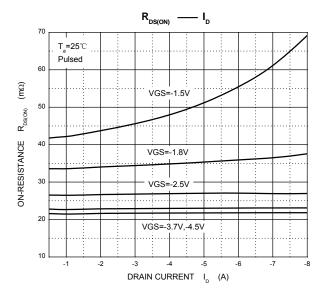
Notes: 1. Pulse test; pulse width≤300µs, duty cycle≤2%.

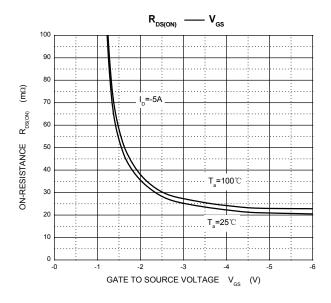
2. Guaranteed by design, not subject to production testing.

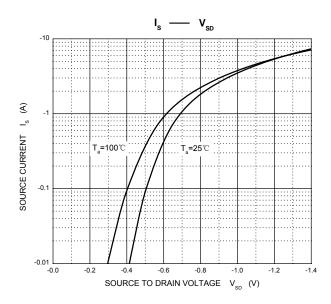
# **Typical Characteristics**

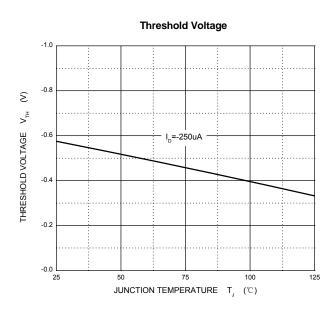




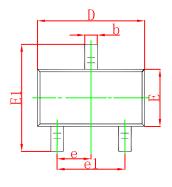


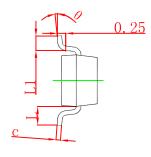


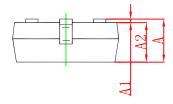




## **SOT-23 Package Outline Dimensions**

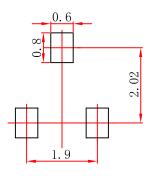






Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Зупівої	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	) TYP	0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550	) REF	0.022	REF	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

## **SOT-23 Suggested Pad Layout**



#### Note:

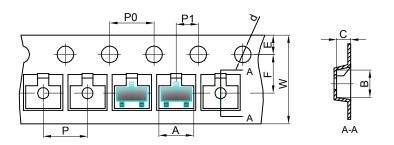
- 1. Controlling dimension: in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

#### NOTICE

JCET reserve the right to make modifications,enhancements, improvements, corrections or other changes without further notice to any product herein.JCET does not assume any liability arising out of the application or use of any product described herein.

# SOT-23 Tape and reel

### SOT-23 Embossed Carrier Tape

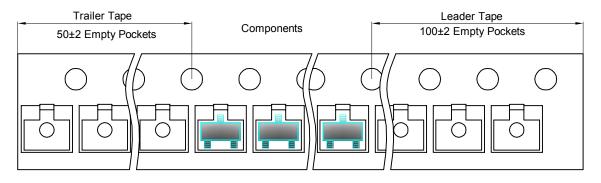


#### Packaging Description:

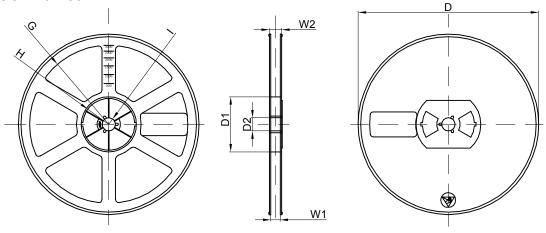
SOT-23 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 17.8cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type A B C d E F P0 P P1 W								W		
SOT-23										

### SOT-23 Tape Leader and Trailer







Dimensions are in millimeter								
Reel Option D D1 D2 G H I W1 W2								W2
7"Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Вох	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	